

2SK1165, 2SK1166

Silicon N-Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

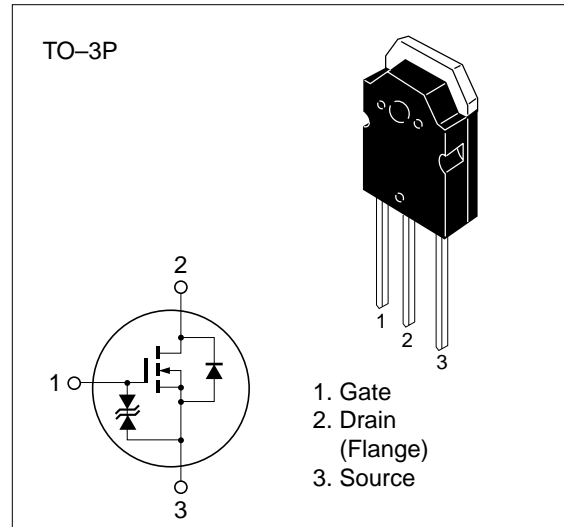


Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	2SK1165	450	V
	2SK1166	500	
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	12	A
Drain peak current	$I_{D(\text{pulse})}^*$	48	A
Body to drain diode reverse drain current	I_{DR}	12	A
Channel dissipation	P_{ch}^{**}	100	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$

** Value at $T_C = 25^\circ\text{C}$

Table 2 Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1165	$V_{(BR)DSS}$	450	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
	2SK1166		500				
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \text{ } \mu\text{A}, V_{DS} = 0$
Gate to source leak current		I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	2SK1165	I_{DSS}	—	—	250	μA	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
	2SK1166						$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	2SK1165	$R_{DS(on)}$	—	0.40	0.55	Ω	$I_D = 6 \text{ A}, V_{GS} = 10 \text{ V}^*$
	2SK1166		—	0.45	0.60		
Forward transfer admittance		$ y_{fs} $	6.0	10	—	S	$I_D = 6 \text{ A}, V_{DS} = 10 \text{ V}^*$
Input capacitance		C_{iss}	—	1450	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		C_{oss}	—	410	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance		C_{rss}	—	55	—	pF	
Turn-on delay time		$t_{d(on)}$	—	20	—	ns	$I_D = 6 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time		t_r	—	70	—	ns	$R_L = 5 \text{ } \Omega$
Turn-off delay time		$t_{d(off)}$	—	120	—	ns	
Fall time		t_f	—	60	—	ns	
Body to drain diode forward voltage		V_{DF}	—	1.0	—	V	$I_F = 12 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time		t_{rr}	—	450	—	ns	$I_F = 12 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

* Pulse Test

